

Serial No.: 10/608,883

Group Art Unit: 2813

### AMENDMENTS TO CLAIMS

- Please amend pending claims 11 and 15 as indicated below. A complete listing of all claims and their status in the application are as follows:

#### Claims 1-10 (canceled)

11. (currently amended) An integrated circuit comprising:  
a semiconductor substrate having a semiconductor device provided thereon;  
a dielectric layer of non-barrier dielectric material capable of being changed into a barrier dielectric material and having ~~a~~an opening provided therein, the dielectric layer around the opening of the barrier dielectric material; and  
a conductor core over the dielectric layer to fill the opening and connect to the semiconductor device.
12. (original) The integrated circuit as claimed in claim 11 wherein the dielectric layer is of SiCOH as the non-barrier dielectric material.
13. (original) The integrated circuit as claimed in claim 11 wherein the dielectric layer is of SiCOH as the non-barrier dielectric material and the dielectric layer is of SiC(H) as the barrier dielectric material.
14. (original) The integrated circuit as claimed in claim 11 wherein the conductor core is of a material from a group consisting of copper, aluminum, gold, silver, a compound thereof, and a combination thereof.
15. (currently amended) An integrated circuit comprising:  
a semiconductor substrate having a semiconductor device provided thereon;  
a dielectric layer of non-barrier dielectric material capable of being reduced into a barrier dielectric material and having ~~a~~an opening provided therein, the dielectric layer around the opening of the barrier dielectric material;  
a seed layer over the dielectric layer to line the opening;  
a conductor core over the seed layer to fill the opening and connect to the semiconductor device; and  
planarizing the conductor core and the seed layer to form a channel.

Serial No.: 10/608,883  
Group Art Unit: 2813

16. (previously presented) The integrated circuit as claimed in claim 15 wherein the dielectric layer is of SiCOH as the non-barrier dielectric material.

17. (previously presented) The integrated circuit as claimed in claim 15 wherein the dielectric layer is of SiCOH as the non-barrier dielectric material and the dielectric layer is of SiC(H) as the barrier dielectric material.

18. (previously presented) The integrated circuit as claimed in claim 15 wherein the seed layer and the conductor core are of a material from a group consisting of copper, aluminum, gold, silver, a compound thereof, and a combination thereof.